

L Number	Hits	Search Text	DB	Time stamp
1	3	(etch\$3 pattern\$4) same (insulat\$3 dielectric) same (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide)) same (sulfuric near3 acid)	USPAT; US-PGPUB	2004/06/27 17:25
2	2147	(etch\$3 pattern\$4) and (insulat\$3 dielectric) and (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide)) and (sulfuric near3 acid)	USPAT; US-PGPUB	2004/06/27 16:23
3	1	(etch\$3 pattern\$4) same (insulat\$3 dielectric) same (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide)) same (sulfuric near3 acid)	EPO; JPO; DERWENT; IBM_TDB	2004/06/27 16:22
4	1	(etch\$3 pattern\$4) and (insulat\$3 dielectric) and (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide)) and (sulfuric near3 acid)	EPO; JPO; DERWENT; IBM_TDB	2004/06/27 16:22
5	293	((etch\$3 pattern\$4) and (insulat\$3 dielectric) and (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide)) and (sulfuric near3 acid)) and gate	USPAT; US-PGPUB	2004/06/27 16:23
6	51	(etch\$3 pattern\$4) same (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide)) same (sulfuric near3 acid)	USPAT; US-PGPUB	2004/06/27 16:52
7	0	plasma same (ammonia nitrogen argon) same (insulat\$3 dielectric) same (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide)) same (sulfuric near3 acid)	USPAT; US-PGPUB	2004/06/27 17:25
8	5	(ammonia nitrogen argon) same (insulat\$3 dielectric) same (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide)) same (sulfuric near3 acid)	USPAT; US-PGPUB	2004/06/27 17:26
9	443	(ammonia nitrogen argon) same (insulat\$3 dielectric) same (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))	USPAT; US-PGPUB	2004/06/27 17:28
10	192	((ammonia nitrogen argon) same (insulat\$3 dielectric) same (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))) and gate	USPAT; US-PGPUB	2004/06/27 17:28
-	5629	(insulat\$3 dielectric) with (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))	USPAT; US-PGPUB	2004/06/27 16:18
-	2164	((insulat\$3 dielectric) with (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))) and (implant\$3 dop\$4)	USPAT; US-PGPUB	2004/06/27 15:01
-	1416	((((insulat\$3 dielectric) with (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))) and (implant\$3 dop\$4)) and ((dop\$3 implant\$6) same (silicon Si germanium Ge argon Ar xenon Xe)))	USPAT; US-PGPUB	2004/06/27 15:01

-	1322	((insulat\$3 dielectric) with (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))) and (implant\$3 dop\$4)) and ((dop\$3 implant\$6) same (silicon Si germanium Ge argon Ar xenon Xe))) and (etch\$3 pattern\$4 remov\$3)	USPAT; US-PGPUB	2004/06/27 13:49
-	916	(((((insulat\$3 dielectric) with (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))) and (implant\$3 dop\$4)) and ((dop\$3 implant\$6) same (silicon Si germanium Ge argon Ar xenon Xe))) and (etch\$3 pattern\$4 remov\$3)) and gate	USPAT; US-PGPUB	2004/06/27 13:56
-	1742	high near5 dielectric near3 gate	USPAT; US-PGPUB	2004/06/27 13:56
-	480	(high near5 dielectric near3 gate) and (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))	USPAT; US-PGPUB	2004/06/27 13:57
-	2977	((insulat\$3 dielectric) with (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide)))	EPO; JPO; DERWENT; IBM_TDB	2004/06/27 15:01
-	88	((insulat\$3 dielectric) with (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))) and (implant\$3 dop\$4)	EPO; JPO; DERWENT; IBM_TDB	2004/06/27 15:01
-	28	((insulat\$3 dielectric) with (ZrO2 HfO2 ("Zr" adj2 "O.sub.2") ("Hf" adj2 "O.sub.2") zirconia hafnia (zirconium near3 oxide)(hafnium near3 oxide))) and (implant\$3 dop\$4)) and ((dop\$3 implant\$6) same (silicon Si germanium Ge argon Ar xenon Xe))	EPO; JPO; DERWENT; IBM_TDB	2004/06/27 15:01